



P-Ch 150V Fast Switching MOSFETs

Description

The HSU15P15 uses advanced trench MOSFET technology to provide excellent $R_{DS(ON)}$ and gate charge for use in a wide variety of other applications.

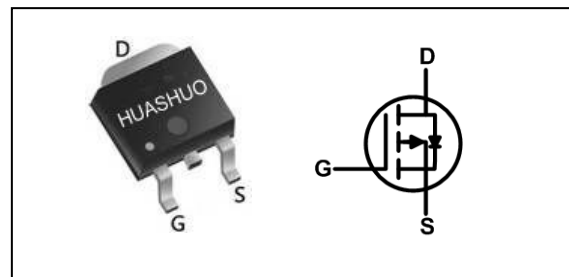
The HSU15P15 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	-150	V
$R_{DS(ON),Max}$	338	m Ω
I_D	-15	A

TO252 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-150	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, V_{GS} @ -10V ¹	-15	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, V_{GS} @ -10V ¹	-9	A
I_{DM}	Pulsed Drain Current ²	-43	A
EAS	Single Pulse Avalanche Energy ³	230	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	90	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	2.8	$^\circ C/W$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-150	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-5A	---	270	338	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-2	-3	-4	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-150V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Q _g	Total Gate Charge	V _{DS} =-75V, V _{GS} =-10V, I _D =-3A	---	40	---	nC
Q _{gs}	Gate-Source Charge		---	5.9	---	
Q _{gd}	Gate-Drain Charge		---	9.2	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-75V, V _{GS} =-10V, R _G =3.3Ω, I _D =-3A	---	25	---	ns
T _r	Rise Time		---	100	---	
T _{d(off)}	Turn-Off Delay Time		---	39	---	
T _f	Fall Time		---	40	---	
C _{iss}	Input Capacitance	V _{DS} =-50V, V _{GS} =0V, f=1MHz	---	1990	---	pF
C _{oss}	Output Capacitance		---	38	---	
C _{rss}	Reverse Transfer Capacitance		---	31.5	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

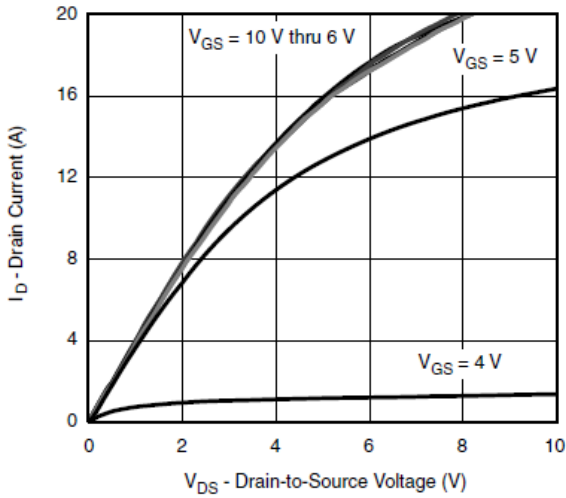
Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

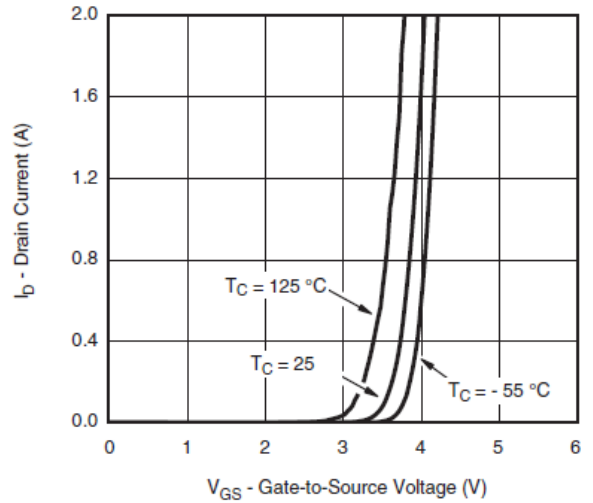


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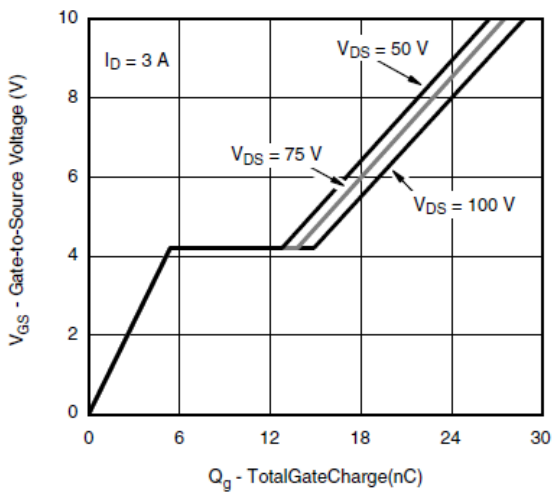
Typical Characteristics



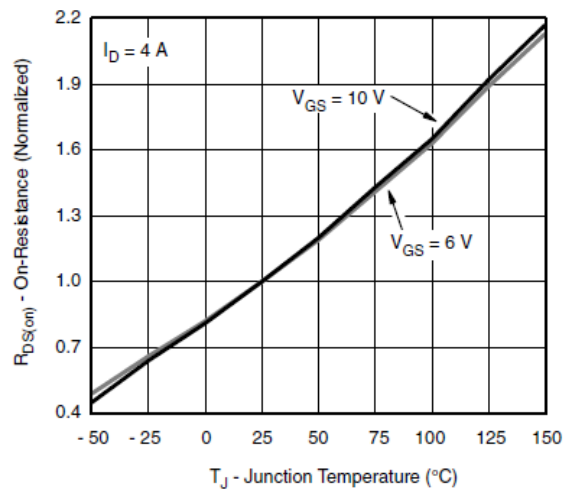
Output Characteristics



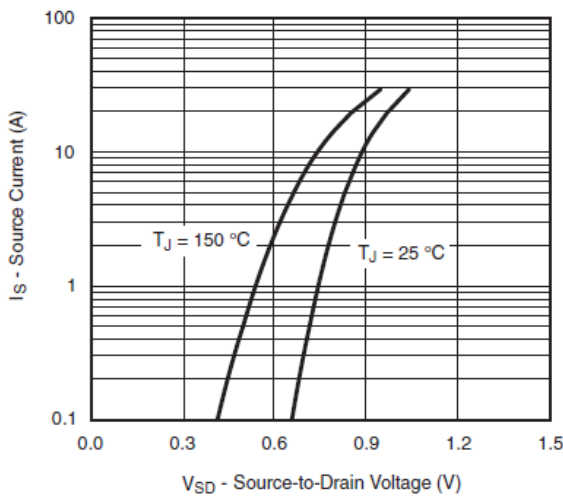
Transfer Characteristics



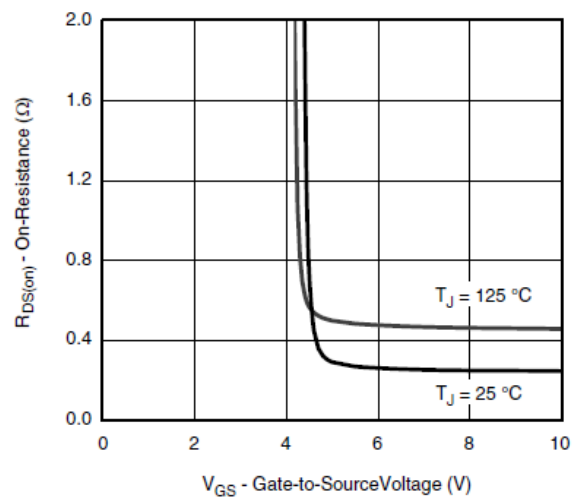
Gate Charge



On-Resistance vs. Junction Temperature



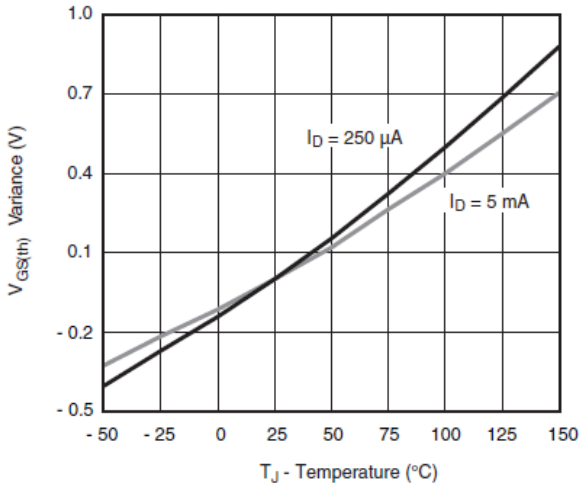
Source-Drain Diode Forward Voltage



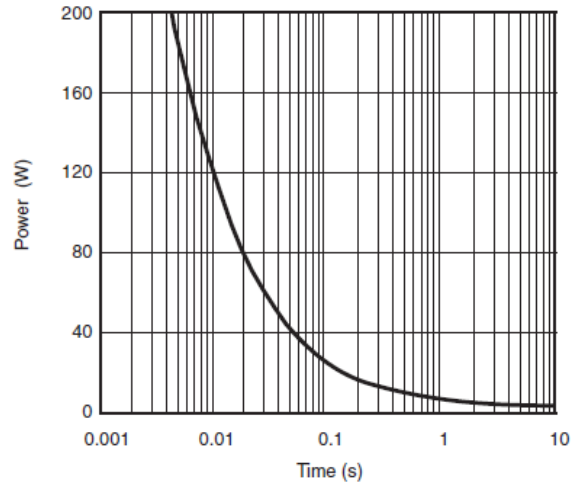
On-Resistance vs. Gate-to-Source Voltage



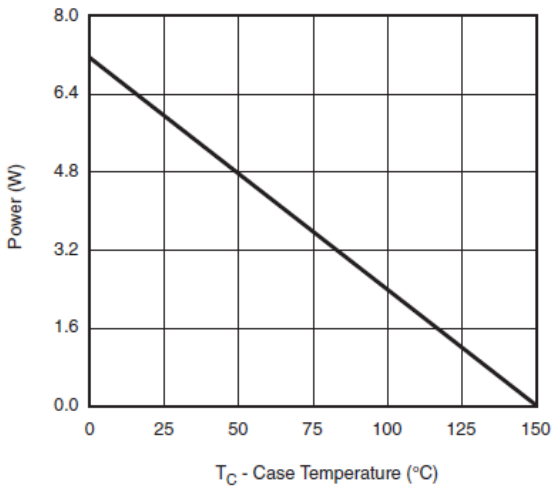
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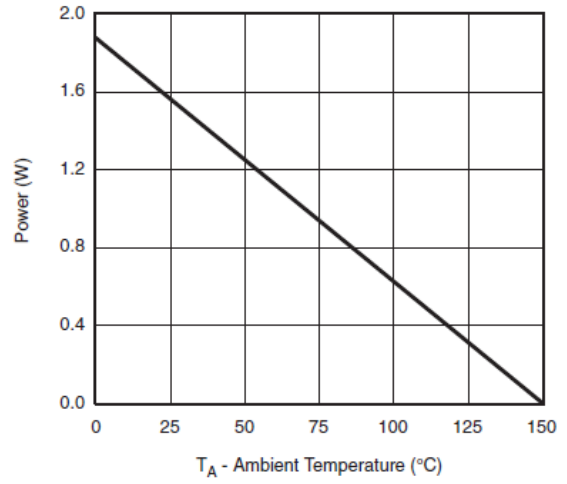
Threshold Voltage



Single Pulse Power, Junction-to-Ambient



Power, Junction-to-Foot

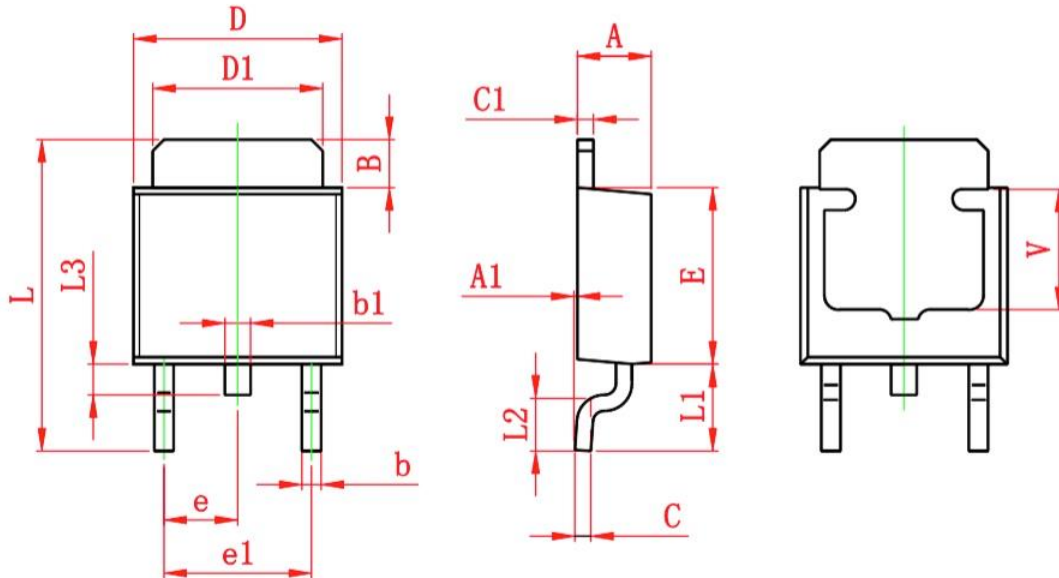


Power, Junction-to-Ambient



Ordering Information

Part Number	Package code	Packaging
HSU15P15	TO252-2	2500/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF.		0.150 REF.	